Amplifier Transistor

NPN Silicon

Features

• Pb–Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CE}	25	Vdc
Collector-Base Voltage	V _{CB}	30	Vdc
Emitter-Base Voltage	V _{EB}	5.0	Vdc
Collector Current – Continuous	۱ _C	200	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	P _D	625 5.0	W mW/°C
Total Device Dissipation @ $T_C = 25^{\circ}C$ Derate above 25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

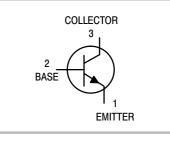
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	83.3	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



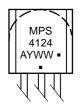
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



= Assembly Location

Y = Year

А

WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPS4124RLRA	TO-92	2000/Tape & Reel
MPS4124RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

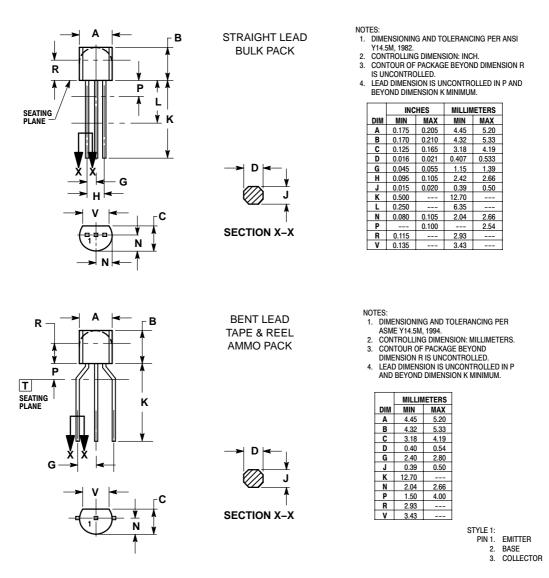
MPS4124

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	· · · · · · · · · · · · · · · · · · ·			
Collector – Emitter Breakdown Voltage ($I_C = 1.0 \text{ mA}, I_B = 0$)	V _{(BR)CEO}	25	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu A, I_E = 0)$	V _{(BR)CBO}	30	-	Vdc
Emitter – Base Breakdown Voltage ($I_C = 0, I_E = 10 \mu A$)	V _{(BR)EBO}	5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ V}, I_E = 0)$	I _{CBO}	_	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ V}, I_C = 0$)	I _{EBO}	_	50	nAdc
ON CHARACTERISTICS				
DC Current Gain $(I_C = 2.0 \text{ mA}, V_{CE} = 1.0 \text{ V})$ $(I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V})$	h _{FE}	120 60	360	-
Collector – Emitter Saturation Voltage $(I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA})$	V _{CE(sat)}	-	0.3	Vdc
Base – Emitter Saturation Voltage $(I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA})$	V _{BE(sat)}	_	0.95	Vdc
SMALL-SIGNAL CHARACTERISTICS	·			•
Current-Gain – Bandwidth Product ($I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}, \text{ f} = 100 \text{ MHz}$)	f _T	170	_	MHz
Output Capacitance $(V_{CB} = 5.0 \text{ V}, I_E = 0, f = 1.0 \text{ MHz})$	C _{ob}	_	4.0	pF
Input Capacitance (V _{EB} = 0.5 V, I_C = 0, f = 1.0 MHz)	C _{ib}	-	13.5	pF
Small–Signal Current Gain (I_C = 2.0 mA, V_{CE} = 1.0 V, f = 1.0 kHz)	h _{fe}	120	480	-
Noise Figure (I _C = 100 μ A, V _{CE} = 5.0 V, R _S = 1.0 kΩ, f = 1.0 kHz)	NF	-	5.0	dB

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



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